

SANYO Semiconductors

DATA SHEET

N-Channel Silicon MOSFET EFC4602 — General-Purpose Switching Device **Applications**

Features

- 2.5V drive.
- · Best suited for LiB charging and discharging switch.
- Common-drain type.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Source-to-Source Voltage	VSSS		20	V
Gate-to-Source Voltage	VGSS		±12	V
Source Current (DC)	IS		6	Α
Source Current (Pulse)	ISP	PW≤100μs, duty cycle≤1%	60	A
Total Dissipation	PT	When mounted on ceramic substrate (5000mm ² ×0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Cumphiel	Conditions		Ratings			Unit
Symbol			min	typ	max	Unit
V(BR)SSS	IS=1mA, VGS=0V	Test Circuit 1	20			V
ISSS	VSS=20V, VGS=0V	Test Circuit 1			1	μΑ
IGSS	VGS=±8V, VSS=0V	Test Circuit 2			±10	μΑ
V _{GS} (off)	V _{SS} =10V, I _S =1mA	Test Circuit 3	0.5		1.3	V
yfs	VSS=10V, IS=3A	Test Circuit 4	4.5	7.5		S
RSS(on)1	IS=3A, VGS=4.5V	Test Circuit 5	19.5	28	36.5	mΩ
RSS(on)2	IS=3A, VGS=4.0V	Test Circuit 5	20	29	38	mΩ
RSS(on)3	IS=1.5A, VGS=3.1V	Test Circuit 5	23	33	43	mΩ
R _{SS} (on)4	IS=1.5A, VGS=2.5V	Test Circuit 5	23	38	53.5	mΩ
	ISSS IGSS VGS(off) yfs RSS(on)1 RSS(on)2 RSS(on)3	V(BR)SSS Is=1mA, VGS=0V ISSS VSS=20V, VGS=0V IGSS VGS=48V, VSS=0V VGS(off) VSS=10V, IS=1mA Jyfs VSS=10V, IS=3A RSS(on)1 IS=3A, VGS=4.5V RSS(on)2 IS=3A, VGS=4.0V RSS(on)3 IS=1.5A, VGS=3.1V	V(BR)SSS IS=1mA, VGS=0V Test Circuit 1 ISSS VSS=20V, VGS=0V Test Circuit 1 IGSS VGS=±8V, VSS=0V Test Circuit 2 VGS(off) VSS=10V, IS=1mA Test Circuit 3 yfs VSS=10V, IS=3A Test Circuit 4 RSS(on)1 IS=3A, VGS=4.5V Test Circuit 5 RSS(on)2 IS=3A, VGS=4.0V Test Circuit 5	V(BR)SSS IS=1mA, VGS=0V Test Circuit 1 20 ISSS VSS=20V, VGS=0V Test Circuit 1 20 IGSS VGS=20V, VGS=0V Test Circuit 1 20 IGSS VGS=±8V, VGS=0V Test Circuit 2 20 VGS(off) VSS=10V, IS=1mA Test Circuit 3 0.5 Jyfs VSS=10V, IS=3A Test Circuit 4 4.5 RSS(on)1 IS=3A, VGS=4.5V Test Circuit 5 19.5 RSS(on)2 IS=3A, VGS=4.0V Test Circuit 5 20 RSS(on)3 IS=1.5A, VGS=3.1V Test Circuit 5 23	Symbol Conditions min typ V(BR)SSS IS=1mA, VGS=0V Test Circuit 1 20 ISSS VSS=20V, VGS=0V Test Circuit 1 20 IGSS VGS=20V, VGS=0V Test Circuit 1 20 VGS(off) VSS=10V, IS=1mA Test Circuit 3 0.5 yfs VSS=10V, IS=3A Test Circuit 4 4.5 7.5 RSS(on)1 IS=3A, VGS=4.5V Test Circuit 5 19.5 28 RSS(on)2 IS=3A, VGS=4.0V Test Circuit 5 20 29 RSS(on)3 IS=1.5A, VGS=3.1V Test Circuit 5 23 33	Symbol Conditions min typ max V(BR)SSS IS=1mA, VGS=0V Test Circuit 1 20 1 ISSS VSS=20V, VGS=0V Test Circuit 1 20 1 ISSS VSS=20V, VGS=0V Test Circuit 1 20 1 IGSS VGS=48V, VGS=0V Test Circuit 2 1 1 VGS(off) VSS=10V, IS=1mA Test Circuit 3 0.5 1.3 yfs VSS=10V, IS=3A Test Circuit 4 4.5 7.5 RSS(on)1 IS=3A, VGS=4.5V Test Circuit 5 19.5 28 36.5 RSS(on)2 IS=3A, VGS=4.0V Test Circuit 5 20 29 38 RSS(on)3 IS=1.5A, VGS=3.1V Test Circuit 5 23 33 43

Marking : FB

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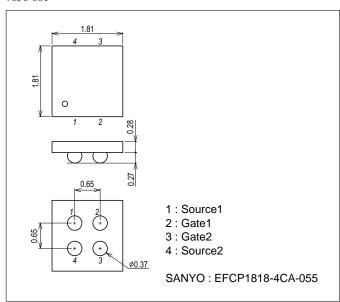
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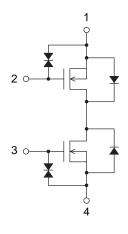
Parameter	Symbol	Conditions		Ratings			Unit
Parameter	Symbol			min	typ	max	Onit
Input Capacitance	Ciss	V _{SS} =10V, f=1MHz	Test Circuit 8		1000		pF
Output Capacitance	Coss	VSS=10V, f=1MHz	Test Circuit 8		180		pF
Reverse Transfer Capacitance	Crss	V _{SS} =10V, f=1MHz	Test Circuit 8		140		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.	Test Circuit 7		23		ns
Rise Time	tr	See specified Test Circuit.	Test Circuit 7		185		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.	Test Circuit 7		160		ns
Fall Time	tf	See specified Test Circuit.	Test Circuit 7		200		ns
Total Gate Charge	Qg	V _{SS} =10V, V _{GS} =10V, I _S =6A			13		nC
Forward Source-to-Source Voltage	VF(S-S)	IS=6A, VGS=0V	Test Circuit 6		0.78	1.2	V

Package Dimensions

unit : mm (typ) 7056-001

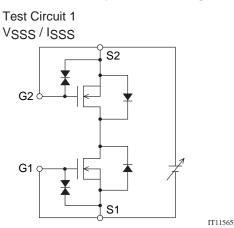


Electrical Connection

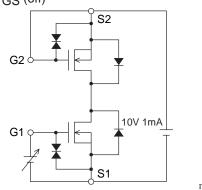


EFC4602

Test Circuits are example of measuring FET1 side

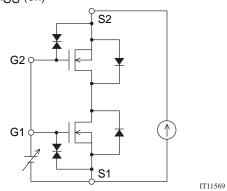


Test Circuit 3 VGS (off)

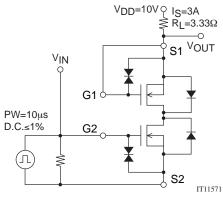


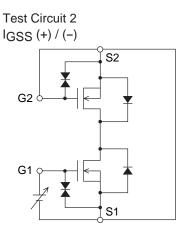
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Test Circuit 5 RSS (on)

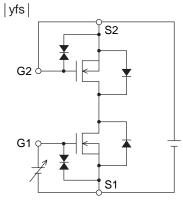


Test Circuit 7 t_d (on), t_r , t_d (off), t_f

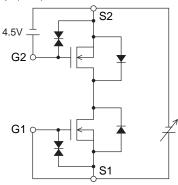




Test Circuit 4



Test Circuit 6 VF (S-S)

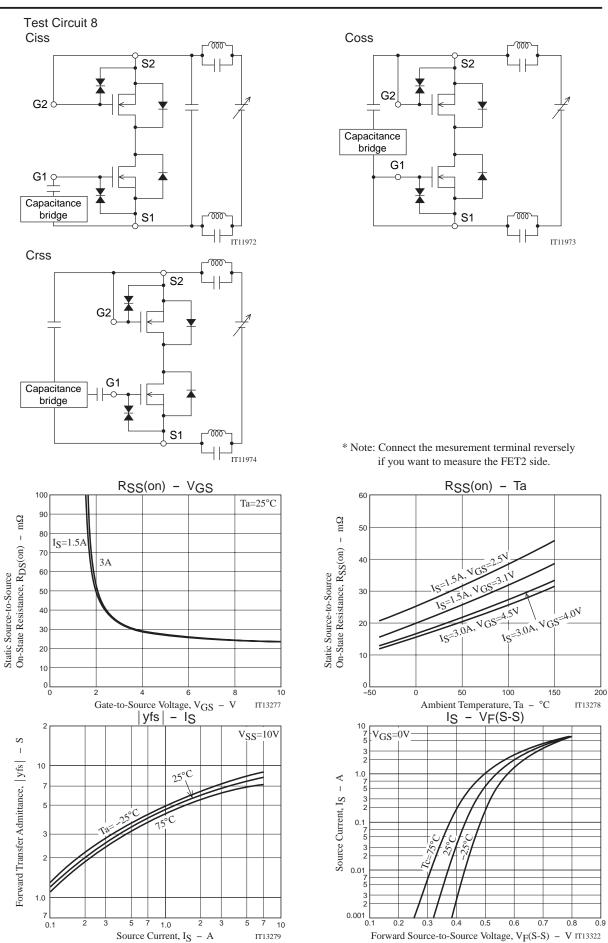


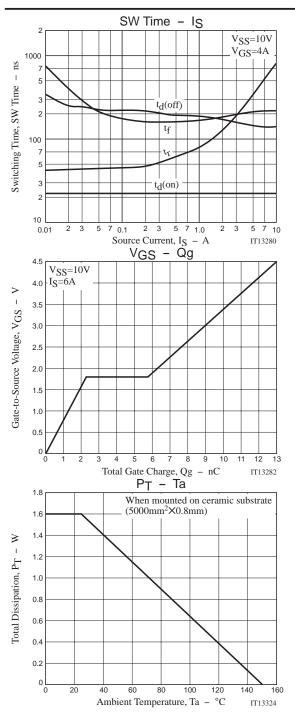
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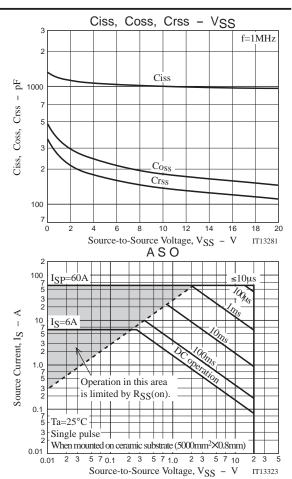
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* Note: Connect the mesurement terminal reversely if you want to measure the FET2 side.







Note on usage : Since the EFC4602 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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